

SILICON NPN POWER TRANSISTOR

TO-66 CASE



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DESCRIPTION:

The CENTRAL SEMICONDUCTOR 2N5202 is a silicon NPN power transistor mounted in a hermetically sealed metal case, designed for general purpose amplifier and switching applications.

MARKING: FULL PART NUMBER

MAXIMUM RATINGS: (T _C =25°C)	SYMBOL		UNITS
Collector-Base Voltage	V _{CBO}	100	V
Collector-Emitter Voltage	VCER	75	V
Collector-Emitter Voltage	V _{CEO}	50	V
Emitter-Base Voltage	V _{EBO}	6.0	V
Continuous Collector Current	۱ _C	4.0	А
Peak Collector Current	ICM	5.0	А
Continuous Base Current	Ι _Β	2.0	А
Power Dissipation	PD	35	W
Operating and Storage Junction Temperature	TJ, Tstg	-65 to +200	°C
Thermal Resistance	ΘJC	5.0	°C/W

ELECTRICAL CHARACTERISTICS: (T_C=25°C unless otherwise noted)

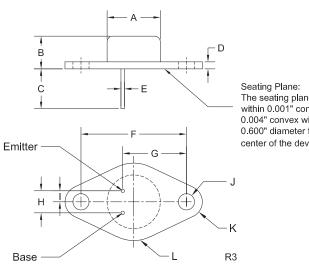
SYMBOL	TEST CONDITIONS	MIN	MAX	UNITS
ICEV	V _{CE} =100V, V _{EB} =1.5V		10	mA
ICEV	V _{CE} =100V, V _{EB} =1.5V, T _C =150°C		10	mA
IEBO	V _{EB} =6.0V		10	mA
BVCEO	I _C =200mA	50		V
BVCER	I _C =200mA, R _{BE} =50Ω	75		V
V _{CE(SAT)}	I _C =4.0A, I _B =400mA		1.2	V
V _{BE(SAT)}	I _C =4.0A, I _B =400mA		2.0	V
h _{FE}	V _{CE} =1.2V, I _C =4.0A	10	100	
h _{fe}	V _{CE} =10V, I _C =500mA	6.0		
Cob	V _{CB} =10V, f=1.0MHz		175	pF
I _{s/b}	V _{CE} =40V, tp=1.0s	400		mA
E _{s/b}	V _{BB} =4.0V, R _{BE} =50Ω, L=50μH	0.4		mJ
^t d	V _{CC} =30V, I _C =4.0A, I _{B1} =I _{B2} =0.8A		40	ns
t _r	V _{CC} =30V, I _C =4.0A, I _{B1} =I _{B2} =0.8A		400	ns
t _s	V _{CC} =30V, I _C =4.0A, I _{B1} =I _{B2} =0.8A		1200	ns
t _f	V _{CC} =30V, I _C =4.0A, I _{B1} =I _{B2} =0.8A		400	ns





2N5202

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TO-66 CASE - MECHANICAL OUTLINE

Seating Plane: The seating plane must be within 0.001" concave to 0.004" convex within 0.600" diameter from the center of the device.

MARKING: FULL PART NUMBER

DIMENSIONS						
	INCHES		MILLIMETERS			
SYMBOL	MIN	MAX	MIN	MAX		
A (DIA)	0.470	0.500	11.94	12.70		
В	0.250	0.340	6.35	8.64		
С	0.360	-	9.14	-		
D	0.050	0.075	1.27	1.91		
E (DIA)	0.028	0.034	0.71	0.86		
F	0.956	0.964	24.28	24.48		
G	0.570	0.590	14.48	14.99		
Н	0.190	0.210	4.83	5.33		
I	0.093	0.107	2.36	2.72		
J (DIA)	0.142	0.152	3.61	3.86		
K (RAD)	0.141		3.58			
L (RAD)	0.345		8.76			
TO-66 (REV:R3)						

R0 (15-January 2019)

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OUTSTANDING SUPPORT AND SUPERIOR SERVICES

PRODUCT SUPPORT

Central's operations team provides the highest level of support to insure product is delivered on-time.

- Supply management (Customer portals)
- Inventory bonding
- Consolidated shipping options

DESIGNER SUPPORT/SERVICES

Central's applications engineering team is ready to discuss your design challenges. Just ask.

- Free guick ship samples (2nd day air)
- Online technical data and parametric search
- SPICE models
- Custom electrical curves
- · Environmental regulation compliance
- Customer specific screening
- · Up-screening capabilities

· Custom product packing

Custom bar coding for shipments

- Special wafer diffusions
- PbSn plating options
- Package details
- Application notes
- · Application and design sample kits
- · Custom product and package development

REQUESTING PRODUCT PLATING

- If requesting Tin/Lead plated devices, add the suffix "TIN/LEAD" to the part number when 1. ordering (example: 2N2222A TIN/LEAD).
- 2. If requesting Lead (Pb) Free plated devices, add the suffix " PBFREE" to the part number when ordering (example: 2N2222A PBFREE).

CONTACT US

Corporate Headquarters & Customer Support Team

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